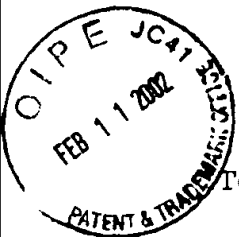


1765



January 25, 2002

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

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TC 1700

Subject: | Serial No. 10/005,803 12/05/01 |
| Hsin-Ching Shih et al. |
| DRY-WET-DRY SOLVENT-FREE PROCESS |
| AFTER STOP LAYER ETCH IN DUAL |
| DAMASCENE PROCESS. |
Grp. Art Unit: 1765

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner of Patents and
Trademarks, Washington, D.C. 20231, on ~~January~~ ^{Feb. 1}, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date SB 2/1/02

U.S. Patent 6,265,320 to Shi et al., "Method of Minimizing Reactive Ion Etch Damage of Organic Insulating Layers in Semiconductor Fabrication," discloses a H₂ plasma post treatment and low k process.

U.S. Patent 5,660,682 to Zhao et al., "Plasma Clean with Hydrogen Gas," discloses a H₂ plasma post clean.

U.S. Patent 6,204,192 to Zhao et al., "Plasma Cleaning Process for Openings Formed in at Least One Low Dielectric Constant Insulation Layer Over Copper Metallization in Integrated Circuit Structures," discloses a plasma clean process.

U.S. Patent 5,882,489 to Bersin et al., "Processes for Cleaning and Stripping Photoresist from Surfaces of Semiconductor Wafers," discloses a method for removing a resist layer, particularly in via holes.

U.S. Patent 5,567,271 to Chu et al., "Oxygen Reactive Ion Etch (RIE) Plasma Method for Removing Oxidized Organic Residues from Semiconductor Substrates," discusses oxygen Reactive Ion Etch (RIE) plasma methods for removing organic residues from semiconductor substrates.

U.S. Patent 6,248,665 to Bao et al., "Delamination Improvement Between Cu and Dielectrics for Damascene Process," discloses a method to improve surface adhesion between copper surfaces and the dielectric that is deposited over these copper surfaces.

U.S. Patent 6,037,664 to Zhao et al., "Dual Damascene Interconnect Structure Using Low Dielectric Constant Material for an Inter-Level Dielectric Layer," discloses a technique for fabricating a dual damascene interconnect structure using a low dielectric constant material as a dielectric layer or layers.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a stylized flourish at the end.

Stephen B. Ackerman,
Reg. No. 37761